



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C	
-20V	$13m\Omega @ V_{GS} = -10V$	-9.3A	
	$16m\Omega @ V_{GS} = -4.5V$	-8.3A	
	$22m\Omega$ @ $V_{GS} = -2.5V$	-7.2A	

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

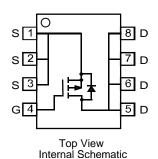
Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Lead Frame. Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.074g (Approximate)





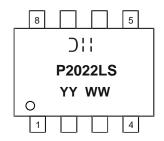
Ordering Information (Note 5)

Ī	Part Number	Compliance	Case	Packaging
	DMP2022LSSQ-13	Automotive	SO-8	2,500/Tape & Reel

Notes

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information



⊃¦¦ = Manufacturer's Marking P2022LS = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 18 = 2018) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±12	V
Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C		-9.3 -7.4	А
Pulsed Drain Current (Note 7)			I _{DM}	-35	А

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	1.6	W
Thermal Resistance, Junction to Ambient	$R_{ hetaJA}$	74	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

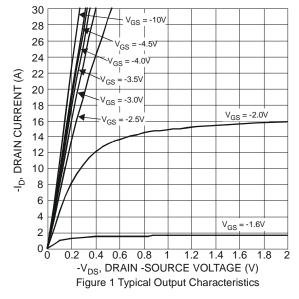
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	-1	μA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}		_	±100	nA	$V_{GS} = \pm 12V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)			•			
Gate Threshold Voltage	V _{GS(TH)}	-0.6	-0.77	-1.1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
		_	8	13	mΩ	$V_{GS} = -10V, I_D = -10A$
Static Drain-Source On-Resistance	R _{DS(ON)}	_	11	16		V _{GS} = -4.5V, I _D = -9A
		_	17	22		$V_{GS} = -2.5V, I_D = -8A$
Forward Transconductance	g fs	_	28	_	S	V _{DS} = -10V, I _D = -10A
Diode Forward Voltage (Note 8)	V_{SD}	-0.5	-0.68	-1.2	V	$V_{GS} = 0V, I_{S} = -3A$
DYNAMIC CHARACTERISTICS (Note 9)			•			
Input Capacitance	C _{iss}	_	2575	_	pF	V _{DS} = -10V, V _{GS} = 0V f = 1MHz
Output Capacitance	Coss		326	_	pF	
Reverse Transfer Capacitance	C _{rss}		261	_	pF	1 - 111112
Gate Resistance	R_{G}	_	10.9	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$
SWITCHING CHARACTERISTICS (Note 9)					-	
Total Gate Charge	Qg	_	28.1 60.2	_		$V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{D} = -10A$ $V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -10A$
Gate-Source Charge	Q _{gs}	_	5.9	_	nC	V _{DS} = -10V, V _{GS} = -10V, I _D = -10A
Gate-Drain Charge	Q _{gd}	_	7.4	_		V _{DS} = -10V, V _{GS} = -10V, I _D = -10A
Turn-On Delay Time	t _{D(ON)}		4.5	15		
Turn-On Rise Time	t _R		3.3	20		$V_{DD} = -15V$, $I_{D} = -1A$, $V_{GS} = -10V$,
Turn-Off Delay Time	t _{D(OFF)}		197	216	ns	$R_{GEN} = 6\Omega$
Turn-Off Fall Time	t _F	_	60.5	153		

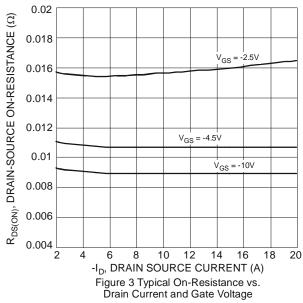
Notes:

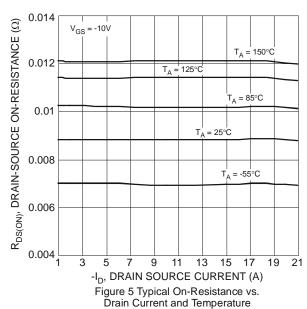
- Device mounted on 2 oz. Copper pads on FR-4 PCB.
- 7. Pulse width $\leq 10 \mu S$, Duty Cycle $\leq 1\%$.
- Fulse water 1996, Buty Gyold 1776.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.

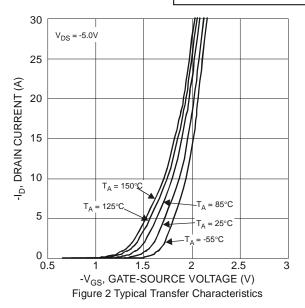


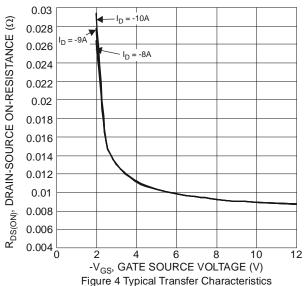












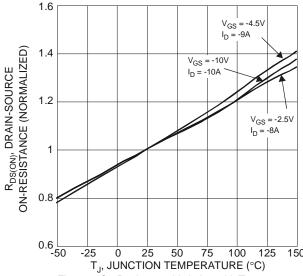
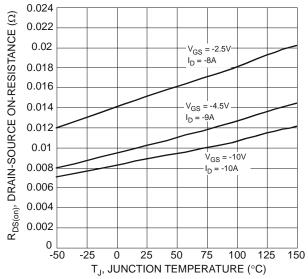
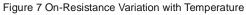


Figure 6 On-Resistance Variation with Temperature









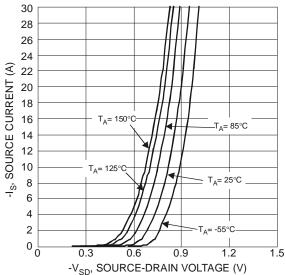
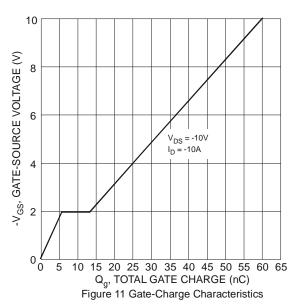
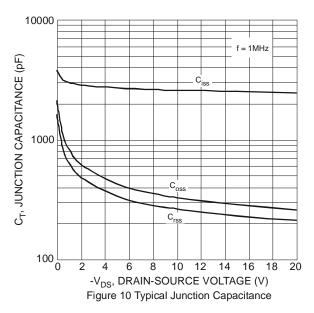


Figure 9 Diode Forward Voltage vs. Current

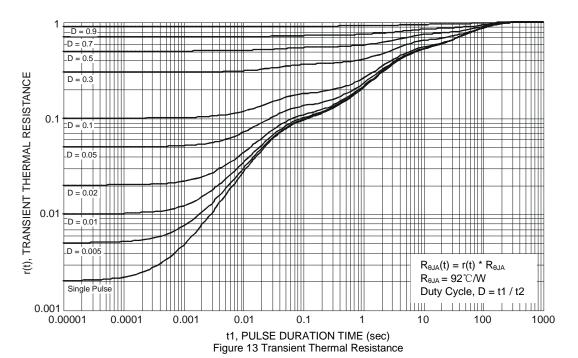


1.4 -V_{GS(ТН)}, GATE THRESHOLD VOLTAGE (V) 1.2 $-I_D = 1mA$ 1 $-I_D = 250 \mu A$ 8.0 0.6 0.4 – -25 0 25 50 75 100 125 150 T_A, AMBIENT TEMPERATURE (°C)

Figure 8 Gate Threshold Variation vs. Ambient Temperature







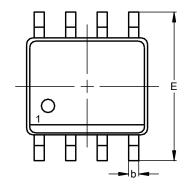
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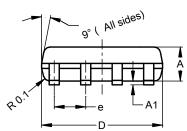


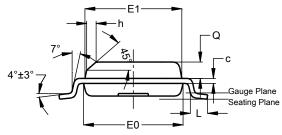
Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SO-8





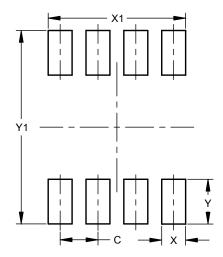


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е			1.27		
h	-		0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

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Dimensions	Value (in mm)			
С	1.27			
X	0.802			
X1	4.612			
Υ	1.505			
Y1	6.50			



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